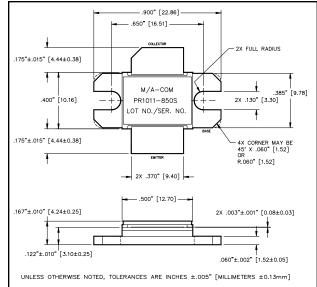
MAPR-001011-850S00

Avionics Pulsed Power Transistor 850W, 1025-1150 MHz, 10µs Pulse, 1% Duty

Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Outline Drawing



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V _{CES}	80	V
Emitter-Base Voltage	V _{EBO}	3.0	V
Collector Current (Peak)	Ι _C	250	А
Power Dissipation @ +25°C	P _{TOT}	11.6	kW
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	TJ	200	°C

Electrical Specifications: $T_c = 25 \pm 5^{\circ}C$ (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 250mA		BV _{CES}	80	-	V
Collector-Emitter Leakage Current	$V_{CE} = 50V$		I _{CES}	-	30	mA
Thermal Resistance	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	R _{TH(JC)}	-	0.015	°C/W
Input Power	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	P _{IN}	-	141	W
Power Gain	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	G _P	7.8	-	dB
Collector Efficiency	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	η _c	42	-	%
Input Return Loss	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	RL	-	-9	dB
Load Mismatch Tolerance	Vcc=50V, Pout=850W	F = 1025 MHz	VSWR-T	-	5:1	-
Load Mismatch Stability *	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	VSWR-S	-	1.5:1	-

* All spurious signals shall be < -60dBc below carrier, except F = Fo $\pm \frac{1}{2}$ Fo shall be < -40dBc

- 1
- ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed. PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples into the troater may be available. Commitment to produce in volume is not guaranteed.
 - North America Tel: 800.366.2266 / Fax: 978.366.2266
 Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
 - Lurope Tel: 44.1908.574.200 / Fax: 44.1908.574.300
 Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 - Astarractific 1et: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.
 COM Technology Solutions and and its affiliates reserve the right to make
 not so the production of th



M/A-COM Products

Released, 30 May 07



Avionics Pulsed Power Transistor 850W, 1025-1150 MHz, 10µs Pulse, 1% Duty

M/A-COM Products Released, 30 May 07

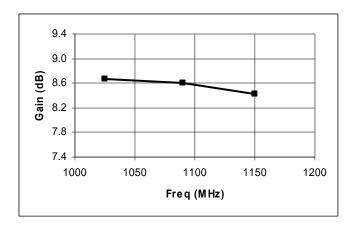
Typical RF Performance

Freq.	Pin	Pout	Gain	∆Gain	lc	Eff	RL	VSWR-S	VSWR-T (5:1)	P1dB Overdrive	
(MHz)	(W)	(W)	(dB)	(dB)	(A)	(%)	(dB)	(1.5:1)		Pout	ΔΡο
1025	116	850	8.67	-	35.3	48.2	-18.3	S	Р	974	0.59
1090	117	850	8.61	-	33.9	50.3	-16.3	S	-	1014	0.76
1150	112	850	8.42	0.25	32.1	53.0	-21.1	S	-	997	0.69

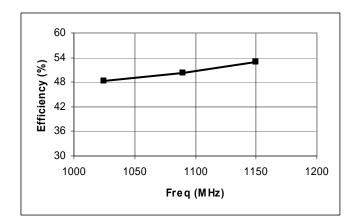
Note: $\Delta Po(dB)$ is the difference between Pout at 1dB overdrive and Pout at Pout=850W.

Gain vs. Frequency

2



Collector Efficiency vs. Frequency

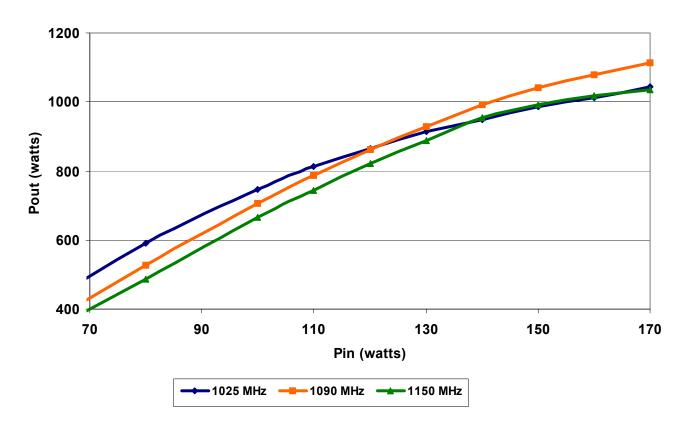






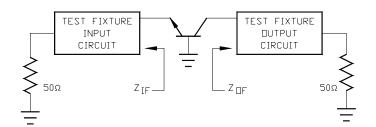
Avionics Pulsed Power Transistor 850W, 1025-1150 MHz, 10µs Pulse, 1% Duty M/A-COM Products Released, 30 May 07

RF Power Transfer Curve (Output Power Vs. Input Power)



Broadband Test Fixture Impedance

F (MHz)	Z _{IF} (Ω)	Z _{OF} (Ω)		
1025	1.7 - j1.8	0.8 - j1.3		
1090	1.4 - j1.2	0.8 - j1.0		
1150	1.3 - j0.7	0.8 - j0.8		



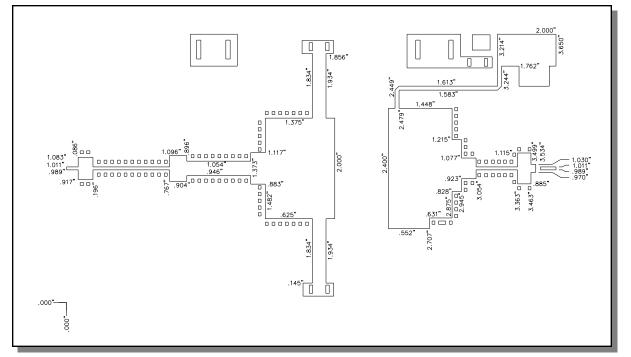
3

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed. **PRELIMINARY**: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples in the protocol of the product size in the product is explained.

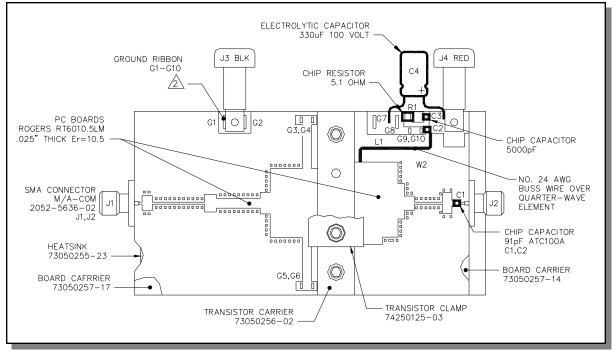
MAPR-001011-850S00

Avionics Pulsed Power Transistor 850W, 1025-1150 MHz, 10µs Pulse, 1% Duty

Test Fixture Circuit Dimensions



Test Fixture Assembly



4





M/A-COM Products Released, 30 May 07